



# FQPF5N60CYDTU Information



For Reference Only

Part Number FQPF5N60CYDTU

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products<br/>Transistors - FETs, MOSFETs - SingleDescriptionMOSFET N-CH 600V 4.5A TO-220F

Package MOSFET N-CH 600V 4.5A TO-220F TO-220-3 Full Pack, Formed Leads

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# FQPF5N60CYDTU Specifications

Manufacturer Part NumberFQPFSN60CYDTUManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackageTO-220-3 Full Pack, Formed LeadsSeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C4.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)33W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 2.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Formed Leads Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Parin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 19nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)  FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.5 Ohm @ 2.25A, 10V Operating Temperature Mounting Type Supplier Device Package TO-220-3 Full Pack, Formed Leads	Manufacturer Part Number	FQPF5N60CYDTU
Package         TO-220-3 Full Pack, Formed Leads           Series         QFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         4.5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         19nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         670pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         33W (Tc)           Rds On (Max) @ Id, Vgs         2.5 Ohm @ 2.25A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220F-3 (Y-Forming)           Package / Case         TO-220-3 Full Pack, Formed Leads	Manufacturer	Fairchild/ON Semiconductor
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Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220F-3 (Y-Forming)  Package / Case  TO-220-3 Full Pack, Formed Leads	Power Dissipation (Max)	33W (Tc)
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Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Formed Leads	Mounting Type	Through Hole
	Supplier Device Package	TO-220F-3 (Y-Forming)
Report errors?	Package / Case	TO-220-3 Full Pack, Formed Leads
		Report errors?

# FQPF5N60CYDTU Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# FQPF5N60CYDTU Payment Methods



















## FQPF5N60CYDTU Shipping Methods













If you have any question about FQPF5N60CYDTU, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com